Listing of Claims:

This listing of claims reflects all claim amendments and replaces all prior versions, and listings, of claims in the application (material to be inserted is in **bold and underline**, and material to be deleted is in ~~strikeout~~ or (if the deletion is of five or fewer consecutive characters or would be difficult to see) in double brackets [[ ]].

1. (Canceled)

2. (Previously Presented) A dielectric thin film prepared by polymerizing an ethylenic-containing precursor with a benzocyclobutane-containing precursor, wherein the ethylenic-containing precursor has a general structure of:

$$P\text{-}(\text{-}Z\text{-}W)_{n^\circ} \qquad (Ia);$$

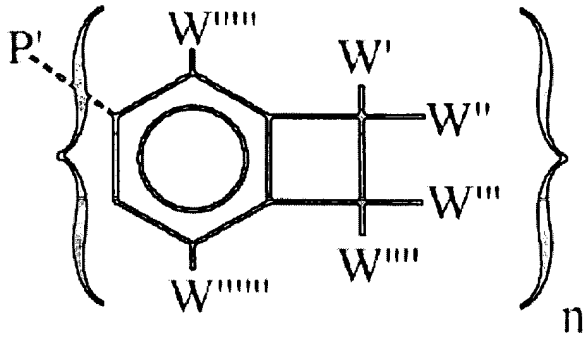
wherein, W is hydrogen, fluorine or a fluorinated phenyl;

P is an aromatic-moiety with a general structure of $-C_6H_{4-n}F_n-$ (n = 0 to 4); $-C_6H_{4-n}F_n-CF_2-C_6H_{4-n}F_n-$ (n = 0 to 4); $-C_{10}H_{6-n}F_n-$ (n = 0 to 6), or $-C_{12}H_{8-n}F_n-$ (n = 0 to 8);

Z is a moiety having an ethylenic group; and

n° is an integer of 2.

3. (Previously Presented) The dielectric thin film of claim 2, wherein the benzyocyclobutane containing precursor has a general structure of:



(IIa')

wherein W', W'', W''', W'''', W''''', and W'''''' are independently the same or different and are hydrogen, fluorine or a fluorinated phenyl;

P' is an aromatic-moiety with a general structure of $-C_6H_{4-n}F_n-$ (n = 0 to 4); $-C_6H_{4-n}F_n-CF_2-C_6H_{4-n}F_n-$ (n = 0 to 4); $-C_{10}H_{6-n}F_n-$ (n = 0 to 6), or $-C_{12}H_{8-n}F_n-$ (n = 0 to 8); and

n' is an integer of 2.

4. (Original) The dielectric thin film of claim 2, wherein the dielectric thin film has a dielectric constant ("ϵ") value equal to or less than 2.6.

5. (Original) The dielectric thin film of claim 2, wherein one or more layers of the thin film is deposited inside an integrated circuit ("IC") or an electronic device.

6. (Original) The dielectric thin film of claim 5, wherein the electronic device comprises an active matrix liquid crystal display, or a fiber optic device.

7. (Original) The dielectric thin film of claim 5, wherein the IC is manufactured via a dual damascene process comprising the dielectric thin film.

8. (Canceled)

9. (Canceled)

10. (Canceled)

11. (Canceled)

12. (Canceled)

13. (Canceled)

14. (Canceled)

15. (Canceled)

16. (Canceled)

17. (Canceled)

18. (Canceled)

19. (Canceled)

20. (Canceled)

21. (Canceled)

22. (Canceled)

23. (Canceled)

24. (Canceled)

25. (Canceled)

26. (Canceled)